

NCE N-Channel Super Trench II Power MOSFET

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

- DC/DC Converter
- •Ideal for high-frequency switching and synchronous rectification

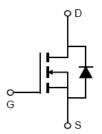
General Features

- V_{DS} =100V, I_D =78A $R_{DS(ON)}$ =6.8m Ω , typical (TO-220)@ V_{GS} =10V $R_{DS(ON)}$ =8.2m Ω , typical (TO-220)@ V_{GS} =4.5V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!







Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP080N10	NCEP080N10	TO-220	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	78	Α
Drain Current-Continuous(T _C =100℃)	I _D (100°C)	55	А
Pulsed Drain Current	I _{DM}	312	А
Maximum Power Dissipation	P _D	120	W
Derating factor		0.8	W/℃
Single pulse avalanche energy (Note 4)	E _{AS}	420	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$

Thermal Characteristic

Thermal Resistance, Junction-to-Case	R ₀ JC	1.25	°C/W
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Electrical Characteristics (T_C=25 [°]C unless otherwise noted)

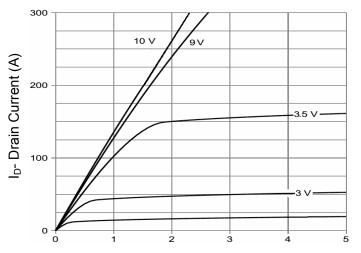
Parameter Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	V _{GS} =0V I _D =250μA 100		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_D=250\mu A$	1.0	1.7	2.5	V
Drain Source On State Registeres	В	V _{GS} =10V, I _D =39A		6.8	8.0	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =39A	-	8.2	9.4	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =37.5A		60	-	S
Dynamic Characteristics (Note3)						
Input Capacitance	C _{lss}	\/ 5 0\/\/ 0\/	-	3650	-	pF
Output Capacitance	Coss	V _{DS} =50V,V _{GS} =0V, F=1.0MHz	-	315	-	pF
Reverse Transfer Capacitance	C _{rss}	F=1.UIVID2	-	22	-	pF
Switching Characteristics (Note 3)						
Turn-on Delay Time	t _{d(on)}		-	15	-	nS
Turn-on Rise Time	t _r	V_{DD} =50 V , I_D =39 A	-	10	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =1.6 Ω	-	34	-	nS
Turn-Off Fall Time	t _f		-	8	-	nS
Total Gate Charge	Qg	\/ _F0\/	-	70	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =50V, I_{D} =39A, V_{GS} =10V	-	14.5	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	16.8	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 2)	V _{SD}	V _{GS} =0V,I _S =39A	-	-	1.2	V
Diode Forward Current	Is		-	-	78	Α
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C$, $I_F = 39A$	-	60	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	106	-	nC

Notes:

- ${\it 1. Repetitive Rating: Pulse width \ limited \ by \ maximum \ junction \ temperature.}$
- 2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 3. Guaranteed by design, not subject to production
- 4. EAS condition : Tj=25 $^{\circ}\text{C}$,V $_{DD}$ =50 V ,V $_{G}$ =10 V ,L=0.25 mH ,Rg=25 Ω

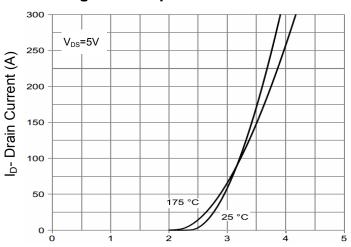


Typical Electrical and Thermal Characteristics



Vds Drain-Source Voltage (V)





Vgs Gate-Source Voltage (V)
Figure 2 Transfer Characteristics

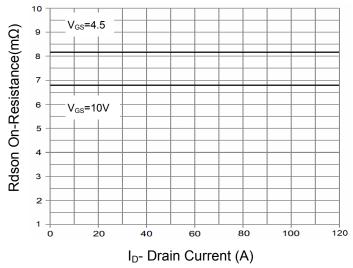


Figure 3 Rdson- Drain Current

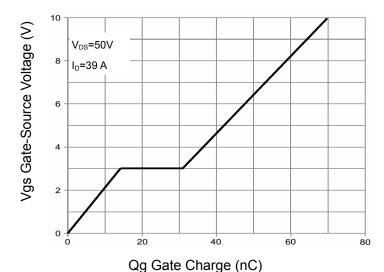


Figure 4 Gate Charge

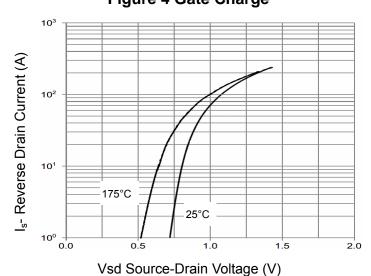


Figure 5 Source- Drain Diode Forward

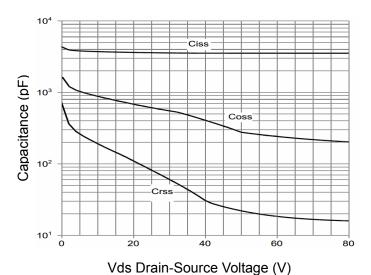
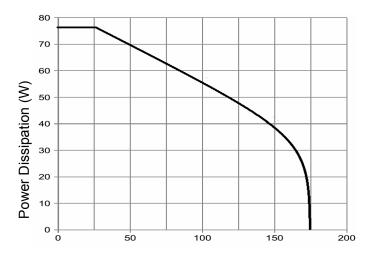
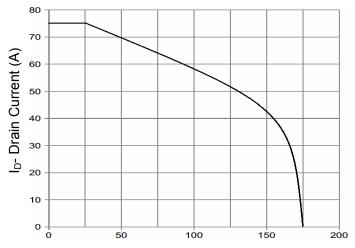


Figure 6 Capacitance vs Vds





T_J-Junction Temperature(°C) **Figure 7 Power De-rating**



T_J-Junction Temperature (°C) **Figure 9 Current De-rating**

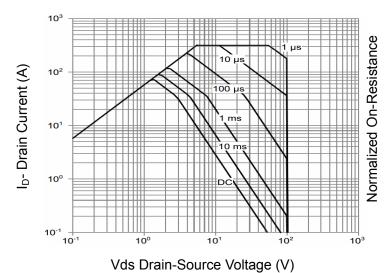


Figure 8 Safe Operation Area

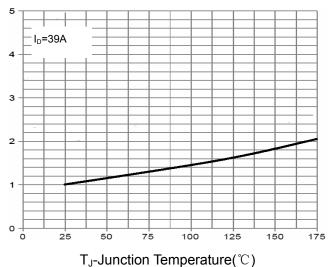
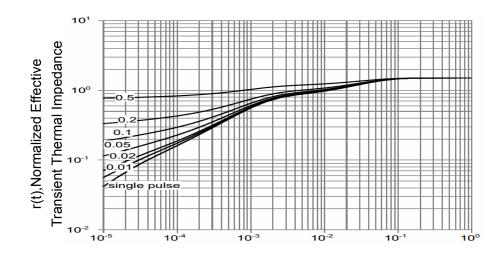


Figure 10 Rdson-Junction Temperature

V2.0

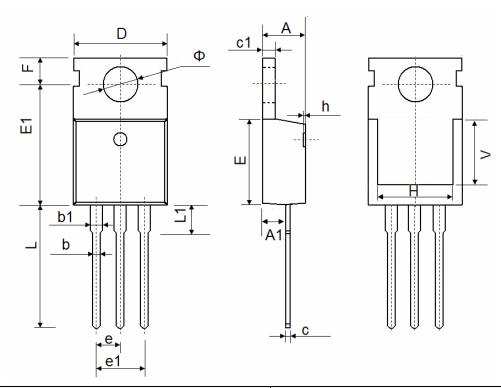


Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



TO-220-3L Package Information



Cumbal	Dimensions	In Millimeters	Dimensions In Inches			
Symbol	Min.	Max.	Min.	Max.		
А	4.400	4.600	0.173	0.181		
A1	2.250	2.550	0.089	0.100		
b	0.710	0.910	0.028	0.036		
b1	1.170	1.370	0.046	0.054		
С	0.330	0.650	0.013	0.026		
c1	1.200	1.400	0.047	0.055		
D	9.910	10.250	0.390	0.404		
Е	8.9500	9.750	0.352	0.384		
E1	12.650	12.950	0.498	0.510		
е	2.540	TYP.	0.100 TYP.			
e1	4.980	5.180	0.196	0.204		
F	2.650	2.950	0.104	0.116		
Н	7.900	8.100	0.311	0.319		
h	0.000	0.300	0.000	0.012		
L	12.900	13.400	0.508	0.528		
L1	2.850	3.250	0.112	0.128		
V	6.900	6.900 REF.		0.276 REF.		
Ф	3.400	3.800	0.134	0.150		



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